

isc Silicon PNP Power Transistors

2SA1220/A

DESCRIPTION

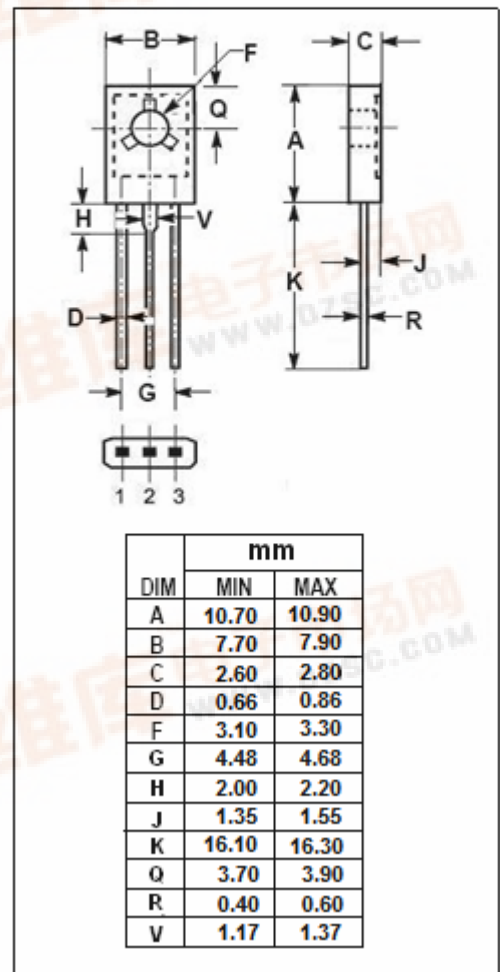
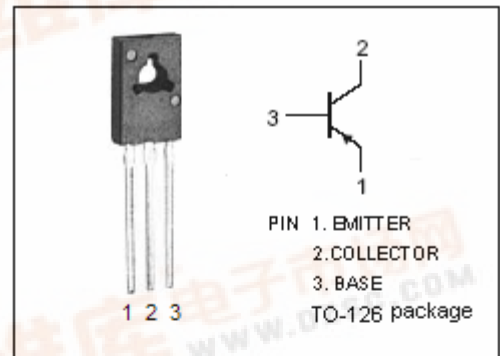
- Good Linearity of h_{FE}
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -120V(\text{Min})-2SA1220$
= $-160V(\text{Min})-2SA1220A$
- Complement to Type 2SC2690/A

APPLICATIONS

- Aaudio frequency power amplifier
- High frequency power amplifier

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT	
V_{CBO}	Collector-Base Voltage	2SA1220	-120	V
		2SA1220A	-160	
V_{CEO}	Collector-Emitter Voltage	2SA1220	-120	V
		2SA1220A	-160	
V_{EBO}	Emitter-Base Voltage	-5	V	
I_C	Collector Current-Continuous	-1.2	A	
I_{CM}	Collector Current-Peak	-2.5	A	
I_B	Base Current-Continuous	-0.3	A	
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.2	W	
	Total Power Dissipation @ $T_C=25^\circ\text{C}$	20		
T_J	Junction Temperature	150	$^\circ\text{C}$	
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$	



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -1A; I_B = -0.2A$			-0.7	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -1A; I_B = -0.2A$			-1.3	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -120V; I_E = 0$			-1.0	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -3V; I_C = 0$			-1.0	μA
h_{FE-1}	DC Current Gain	$I_C = -5mA; V_{CE} = -5V$	35			
h_{FE-2}	DC Current Gain	$I_C = -0.3A; V_{CE} = -5V$	60		320	
f_T	Current-Gain—Bandwidth Product	$I_C = -0.2A; V_{CE} = -5V$		175		MHz
C_{OB}	Output Capacitance	$I_E = 0; V_{CB} = -10V; f_{test} = 1.0MHz$		26		pF

◆ h_{FE-2} Classifications

R	Q	P
60-120	100-200	160-320